SILICON TRANSISTORS 2SD1615, 2SD1615A

NPN SILICON EPITAXIAL TRANSISTORS POWER MINI MOLD

DESCRIPTION

EC

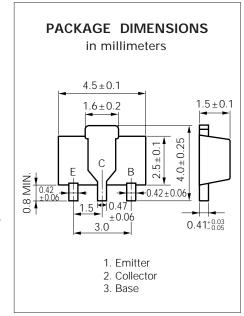
2SD1615, 1615A are designed for audio frequency power amplifier and switching application, especially in Hybrid Integrated Circuits.

FEATURES

- World Standard Miniature Package
- Low VCE (sat) VCE(sat) = 0.15 V
- Complement to 2SB1115, 2SD1115A

ABSOLUTE MAXIMUM RATINGS

| Maximum Voltages and Currents (T _A = 25 | °C) | 2SD1615 | 2SD1615/ | 4 |
|--|------|---------|----------|----|
| Collector to Base Voltage | Vсво | 60 | 120 | V |
| Collector to Emitter Voltage | Vceo | 50 | 60 | V |
| Emitter to Base Voltage | Vево | 6 | 5 | Α |
| Collector Current (DC) | lc | - | 1 | Α |
| Collector Current (Pulse)* | lc | - | 2 | Α |
| Maximum Power Dissipation | | | | |
| Total Power Dissipation | | | | |
| at 25 °C Ambient Temperature** | Рт | 2 | .0 | W |
| Maximum Temperatures | | | | |
| Junction Temperature | Tj | 15 | 50 | °C |
| Storage Temperature Range | Tstg | –55 to | +150 | °C |
| | | | | |



* PW \leq 10 ms, Duty Cycle \leq 50 %

** When mounted on ceramic substrate of 16 $cm^2 \times 0.7$ mm

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | | TEST CONDITIONS |
|------------------------------|-------------|------|------|------|------|---|--------------------------------|
| Collector Cutoff Current | Ісво | | | 100 | nA | 2SD1615 | $V_{CB} = 60 V, I_E = 0$ |
| | | | | 100 | nA | 2SD1615A | $V_{CB} = 120 V, I_E = 0$ |
| Emitter Cutoff Current | Ево | | | 100 | nA | VEB = 6.0 V, Ic = 0 | |
| DC Current Gain | hfe1*** | 135 | 290 | 600 | | 2SC1615 | $V_{CE} = 2.0 V$, Ic = 100 mA |
| | | 135 | | 400 | | 2SD1615A | |
| DC Current Gain | hfe2*** | 81 | 270 | | | Vce = 2.0 V, Ic = 1.0 A | |
| Collector Saturation Voltage | VCE(sat)*** | | 0.15 | 0.3 | V | Ic = 1.0 A, I _B = 50 mA | |
| Base Saturation Voltage | VBE(sat)*** | | 0.9 | 1.2 | V | Ic = 1.0 A, IB = 50 mA | |
| Base to Emitter Voltage | VBE*** | 600 | | 700 | mV | Vce = 2.0 V, Ic = 50 mA | |
| Gain Bandwidth Product | f⊤ | 80 | 160 | | MHz | Vce = 2.0 V, Ie = -100 mA | |
| Output Capacitance | Cob | | 19 | | рF | $V_{CB} = 10 V$, $I_E = 0$, $f = 1.0 MHz$ | |

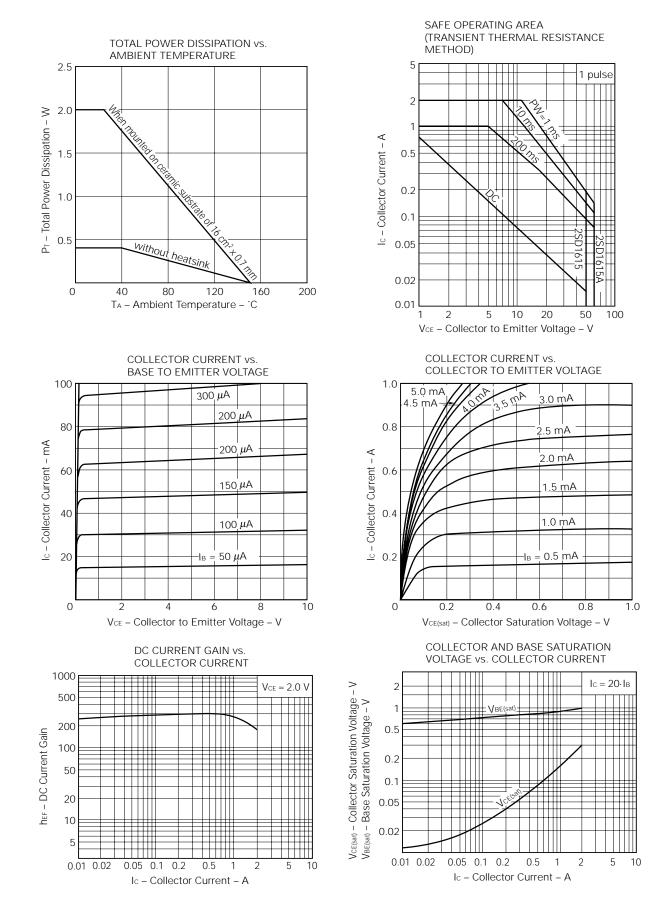
*** Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

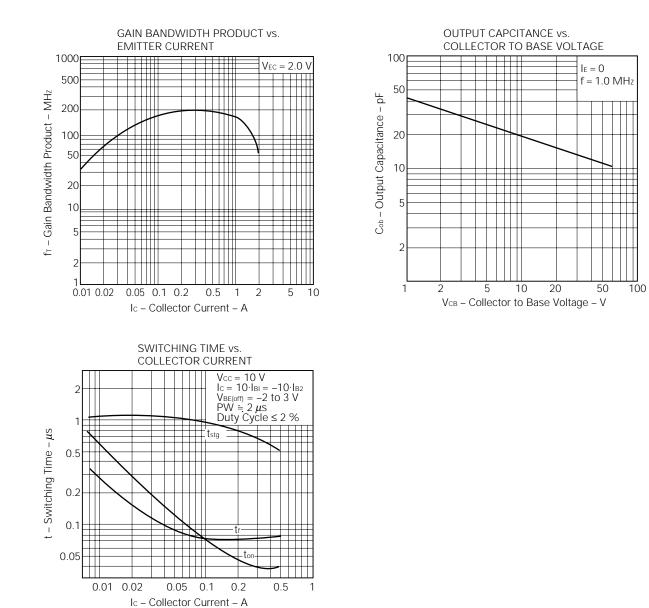
hFE Classification

| MARKING | 2SD1615 | GM | GL | GK |
|---------|----------|------------|------------|------------|
| | 2SD1615A | GQ | GP | |
| h | FE | 135 to 270 | 200 to 400 | 300 to 600 |

Document No. D10198EJ3V0DSD0 (3rd edition) (Previous No. TC-5810A) Date Published June 1995 P Printed in Japan

TYPICAL CHARACTERISTICS (T_A = 25 °C)





REFERENCE

| Document Name | Document No. | | |
|--|--------------|--|--|
| NEC semiconductor device reliability/quality control system. | TEI-1202 | | |
| Quality grade on NEC semiconductor devices. | IEI-1209 | | |
| Semiconductor device mounting technology manual. | IEI-1207 | | |
| Semiconductor device package manual. | IEI-1213 | | |
| Guide to quality assurance for semiconductor devices. | MEI-1202 | | |
| Semiconductor selection guide. | MF-1134 | | |

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